TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

TC7MH257FK

Quad 2-Channel Multiplexer (3-State)

The TC7MH257FK is an advanced high speed CMOS multiplexer fabricated with silicon gate C^2 MOS technology.

It achieves the high speed operation similar to equivalent bipolar schottky TTL while maintaining the CMOS low power dissipation.

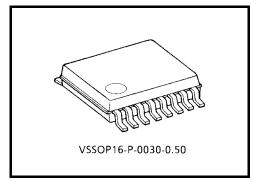
It is composed of four independent 2-channel multiplexers with common SELECT and $\overline{OUTPUTENABLE}$ (\overline{OE}).

If \overline{OE} is set low, the outputs are held in a high-impedance state. When SELECT is set low, "A" data inputs are enabled.

Conversely, when SELECT is high, "B" data inputs are enabled.

An input protection circuit ensures that 0 to 5.5 V can be applied to the input pins without regard to the supply voltage.

This device can be used to interface 5 V to 3 V systems and two supply systems such as battery back up. This circuit prevents device destruction



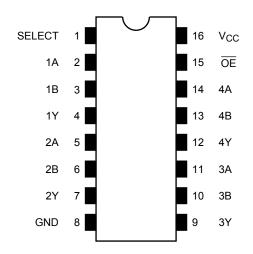
Weight: 0.02 g (typ.)

supply systems such as battery back up. This circuit prevents device destruction due to mismatched supply and input voltages.

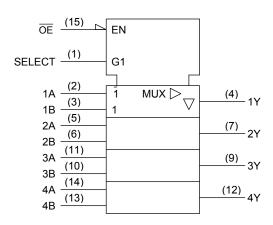
Features

- High speed: $t_{pd} = 3.6 \text{ ns (typ.)} (V_{CC} = 5 \text{ V})$
- Low power dissipation: $I_{CC} = 4 \mu A \text{ (max) (Ta} = 25 ^{\circ}\text{C)}$
- High noise immunity: V_{NIH} = V_{NIL} = 28% V_{CC} (min)
- Power down protection is provided on all inputs.
- Balanced propagation delays: $t_{pLH} \approx t_{pHL}$
- Wide operating voltage range: $V_{CC (opr)} = 2 \sim 5.5 \text{ V}$
- Low noise: $V_{OLP} = 0.8 \text{ V (max)}$
- Pin and function compatible with 74ALS257

Pin Assignment (top view)



IEC Logic Symbol



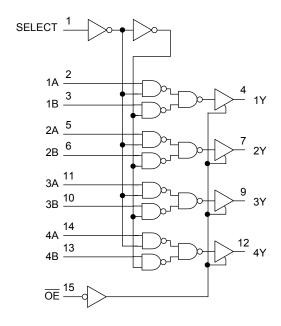
Truth Table

	Outputs					
ŌĒ	Select	Α	В	Outputs		
Н	Х	Х	Х	Z		
L	L	L	Х	L		
L	L	Н	Х	Н		
L	Н	Х	L	L		
L	Н	Х	Н	Н		

X: Don't care

Z: High impedance

System Diagram





Absolute Maximum Ratings (Note)

Characteristics	Symbol	Rating	Unit
Supply voltage range	V _{CC}	-0.5~7.0	V
DC input voltage	V _{IN}	-0.5~7.0	V
DC output voltage	V _{OUT}	-0.5~V _{CC} + 0.5	V
Input diode current	I _{IK}	-20	mA
Output diode current	I _{OK}	±20	mA
DC output current	lout	±25	mA
DC V _{CC} /ground current	I _{CC}	±50	mA
Power dissipation	P _D	180	mW
Storage temperature	T _{stg}	-65~150	°C

Note: Exceeding any of the absolute maximum ratings, even briefly, lead to deterioration in IC performance or even destruction.

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings and the operating ranges.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Operating Ranges (Note)

Characteristics	Symbol	Rating	Unit	
Supply voltage	V _{CC}	2.0~5.5	V	
Input voltage	V _{IN}	0~5.5	V	
Output voltage	Vout 0~Vcc		V	
Operating temperature	T _{opr}	-40~85	°C	
Input rise and fall time	dt/dv	$0\sim100~(V_{CC}=3.3\pm0.3~V)$	ns/V	
input rise and rail time	avav	$0~20~(V_{CC} = 5 \pm 0.5~V)$	113/ V	

Note: The operating ranges must be maintained to ensure the normal operation of the device. Unused inputs must be tied to either VCC or GND.

Electrical Characteristics

DC Characteristics

Characteristics		Symbol Test Condition		Ta = 25°C			Ta = -40~85°C		Unit		
		Symbol	1650	rest Condition		Min	Тур.	Max	Min	Max	Offic
					2.0	1.50	_	_	1.50		
High level Input voltage		V_{IH}	_		3.0~5.5	V _{CC} × 0.7	ı		V _{CC} × 0.7		V
input voitage					2.0			0.50		0.50	v
	Low level	V_{IL}		_		_	_	V _{CC} × 0.3	_	$\begin{array}{c} V_{CC} \\ \times \ 0.3 \end{array}$	
					2.0	1.9	2.0		1.9		V
		Vон	V _{IN} = V _{IH} or V _{IL}	$I_{OH} = -50 \mu A$	3.0	2.9	3.0		2.9		
	High level				4.5	4.4	4.5		4.4		
Output voltage				$I_{OH} = -4 \text{ mA}$	3.0	2.58			2.48		
				$I_{OH} = -8 \text{ mA}$	4.5	3.94	_	_	3.80		
Output voltage			V _{IN} = V _{IH} or V _{IL}	Ι _{ΟL} = 50 μΑ	2.0	_	0	0.1	_	0.1	
					3.0		0	0.1	_	0.1	
	Low level	V_{OL}			4.5		0	0.1	_	0.1	
				$I_{OL} = 4 \text{ mA}$	3.0	_	_	0.36	_	0.44	
			$I_{OL} = 8 \text{ mA}$	4.5	_	_	0.36	_	0.44		
3-state output off-state current I _{OZ}		l _{OZ}	$V_{IN} = V_{IH}$ or V_{IL} $V_{OUT} = V_{CC}$ or GND		5.5	_	_	±0.25		±2.50	μА
Input leakage cu	Input leakage current I _{IN} V _{IN} = 5.5 V or GND		/ or GND	0~5.5	_	_	±0.1		±1.0	μΑ	
Quiescent supply current		Icc	V _{IN} = V _{CC} or GND		5.5	_	_	4.0		40.0	μΑ

AC Characteristics (Input: $t_r = t_f = 3$ ns)

Characteristics	Symbol	Test Condition			Ta = 25°C			Ta = -40~85°C		Unit
Characteristics	Symbol	rest Condition	V _{CC} (V)	C _L (pF)	Min	Тур.	Max	Min	Max	Onit
_			3.3 ± 0.3	15	_	5.8	9.3	1.0	11.0	ns
Propagation delay time	t _{pLH}			50		8.3	12.8	1.0	14.5	
(A, B-Y)	tpHL	_	5.0 ± 0.5	15		3.6	5.9	1.0	7.0	113
			3.0 ± 0.5	50		5.1	7.9	1.0	9.0	
			3.3 ± 0.3	15		7.0	11.0	1.0	13.0	
Propagation delay time	t _{pLH}	_	3.3 ± 0.3	50		9.5	14.5	1.0	16.5	ns
(SELECT-Y)	tpHL		5.0 ± 0.5	15		4.0	6.8	1.0	8.0	
				50		5.5	8.8	1.0	10.0	
	t _{pZL} t _{pZH}	$R_L = 1 \text{ k}\Omega$	3.3 ± 0.3	15		6.7	10.5	1.0	12.5	- - ns
3-state output enable time				50		9.2	14.0	1.0	16.0	
3-state output enable time			5.0 ± 0.5	15		3.6	6.8	1.0	8.0	
			5.0 ± 0.5	50		5.1	8.8	1.0	10.0	
3-state output disable time	t _{pLZ} t _{pHZ}	R _L = 1 kΩ	3.3 ± 0.3	50		8.6	12.0	1.0	13.5	ns
5-state output disable time			5.0 ± 0.5	50		5.7	7.9	1.0	9.0	115
Input capacitance	C _{IN}	-	_			4	10	_	10	pF
Output capacitance	C _{OUT}					6	_		_	pF
Power dissipation capacitance	C _{PD}			(Note)	_	23	_	_	_	pF

Note: C_{PD} is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

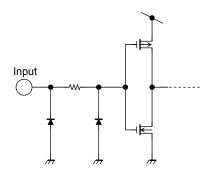
Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD} \cdot V_{CC} \cdot f_{IN} + I_{CC}/4 \text{ (per bit)}$

Noise Characteristics (Input: $t_r = t_f = 3$ ns)

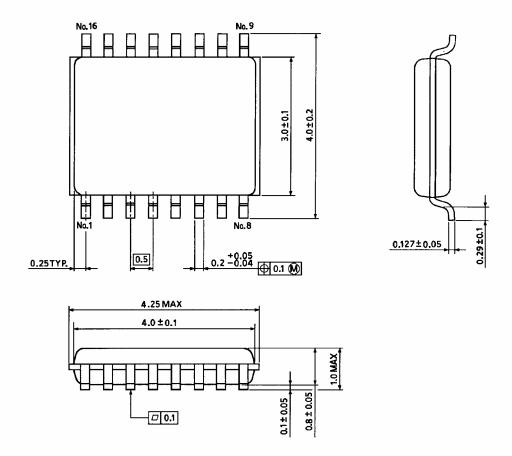
Characteristics	Symbol	Test Condition		Ta = 25°C		Unit
Characteristics	Syllibol	Test Condition	V _{CC} (V)	Тур.	Limit	UIIIL
Quiet output maximum dynamic V _{OL}	V _{OLP}	C _L = 50 pF	5.0	0.3	0.8	V
Quiet output minimum dynamic V _{OL}	V _{OLV}	C _L = 50 pF	5.0	-0.3	-0.8	V
Minimum high level dynamic input voltage $V_{\mbox{\scriptsize IH}}$	V _{IHD}	C _L = 50 pF	5.0	_	3.5	V
Maximum low level dynamic input voltage V_{IL}	V _{ILD}	C _L = 50 pF	5.0	_	1.5	V

Input Equivalent Circuit



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Package Dimensions



Weight: 0.02 g (typ.)

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20070701-EN GENERAL

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